NEC

MOS INTEGRATED CIRCUIT

μPD431008

1M-BIT CMOS FAST STATIC RAM
128K-WORD BY 8-BIT

Description

The μPD431008 is a high speed, low power, 1 048 576 bits (131 072 words by 8 bits) CMOS static RAM.
The μPD431008 is packed in 32-pin plastic SOJ.

Feature

- 131 072 words by 8 bits organization
- Fast access time 15, 17, 20 ns (MAX.)
- Output buffers control: $\overline{OE}$
- Common I/O using three state outputs
- Fully static operation: no clock or refreshing to operate
- TTL compatible: all inputs and outputs
- Single +5 V power supply

Ordering Information

Part number	Package	Access time ns (MAX.)	Operating supply current mA (MAX.)	Standby supply current mA (MAX.)	Quality grade
μPD431008LE-15	32-pin plastic SOJ (400 mil)	15	160	10	Standard
μPD431008LE-17		17	150		
μPD431008LE-20		20	140		

Remark Operating supply current is 120 mA (MAX.) when this product is used at 50ns cycle time.

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

The information in this document is subject to change without notice.

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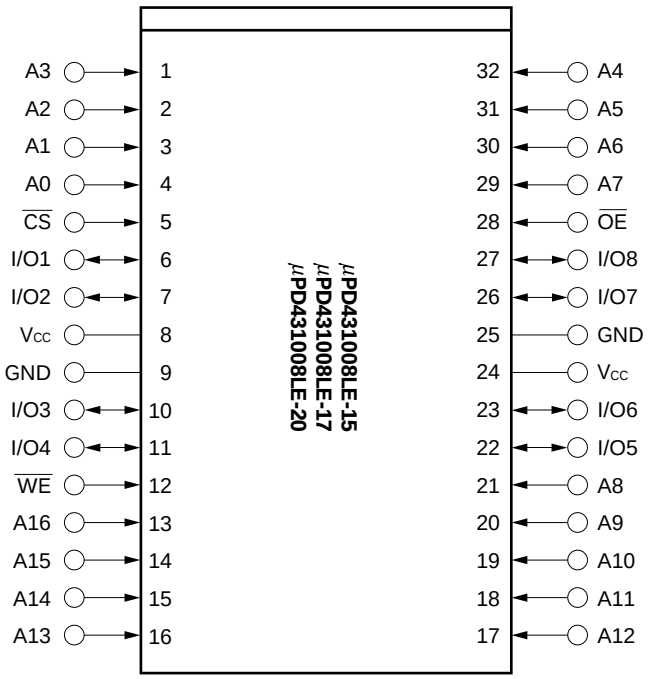
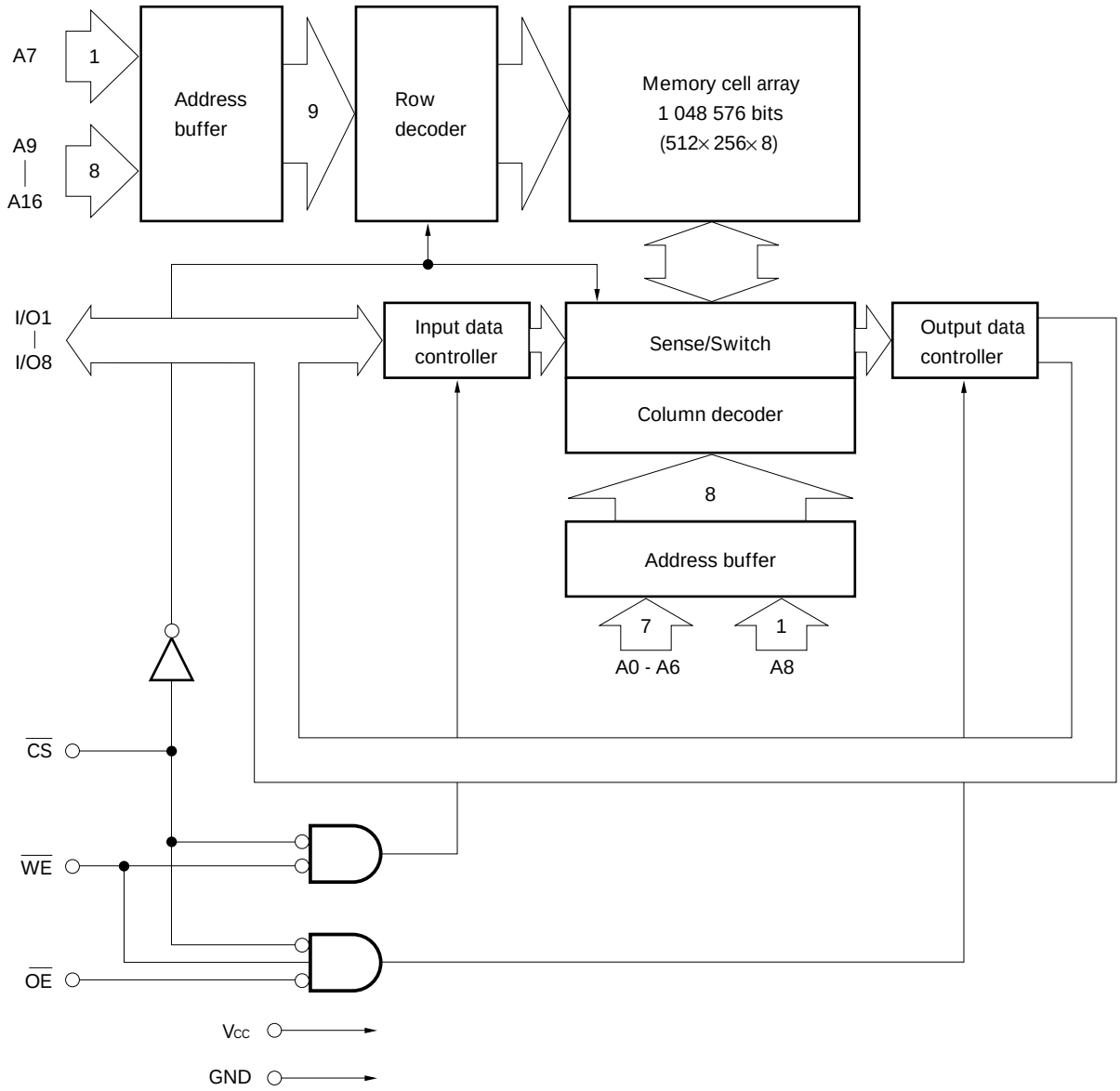
Pin Configuration (Marking Side)

32-Pin Plastic SOJ (400 mil)



A0 – A16	:	Address Inputs
I/O1 – I/O8	:	Data Inputs/Outputs
$\overline{CS}$	:	Chip Select
$\overline{WE}$	:	Write Enable
$\overline{OE}$	:	Output Enable
V_{CC}	:	Power Supply
GND	:	Ground

Block Diagram



Truth Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	I/O	Supply current
H	×	×	Not selected	Hi-Z	I_{SB}
L	L	H	Read	D_{OUT}	I_{CC}
L	×	L	Write	D_{IN}	
L	H	H	Output disable	Hi-Z	

Remark × : Don't care

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC}	−0.5[Note] to +7.0	V
Input/Output voltage	V_T	−0.5 [Note] to V_{CC} +0.5	V
Operating temperature	T_{opt}	0 to +70	°C
Storage temperature	T_{stg}	−55 to +125	°C

Note −3.0 V (MIN.) (Pulse width: 10 ns)

Recommended Operating Conditions

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage	V_{CC}	4.5	5.0	5.5	V
High level input voltage	V_{IH}	2.2		V_{CC} +0.5	V
Low level input voltage	V_{IL}	−0.5[Note]		+0.8	V
Ambient temperature	T_a	0		+70	°C

Note −3.0 V (MIN.) (Pulse width: 10 ns)

DC Characteristics (Recommended operating conditions unless otherwise noted)

Parameter	Symbol	Test conditions		MIN.	TYP.	MAX.	Unit
Input leakage current	I_{LI}	V_{IN} = 0 V to V_{CC}		−2		+2	μA
Output leakage current	I_{LO}	$V_{I/O}$ = 0 V to V_{CC}, $\overline{CS}$ = V_{IH} or $\overline{OE}$ = V_{IH} or $\overline{WE}$ = V_{IL}		−2		+2	μA
Operating supply current	I_{CC}	$\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA	Cycle time: 15 ns			160	mA
			Cycle time: 17 ns			150	
			Cycle time: 20 ns			140	
			Cycle time: 50 ns			120	
Standby supply current	I_{SB}	$\overline{CS}$ = V_{IH}, V_{IN} = V_{IH} or V_{IL}				30	mA
	I_{SB1}	V_{CC} − 0.2 V ≦ $\overline{CS}$, V_{IN} ≦ 0.2 V or V_{CC} − 0.2 V ≦ V_{IN}				10	
High level output voltage	V_{OH}	I_{OH} = −4.0 mA		2.4			V
Low level output voltage	V_{OL}	I_{OL} = 8 mA				0.4	V

Remark V_{IN}: Input voltage

Capacitance (T_a = +25 °C, f = 1 MHz)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C_{IN}	V_{IN} = 0 V			6	pF
Input/Output capacitance	$C_{I/O}$	$V_{I/O}$ = 0 V			8	pF

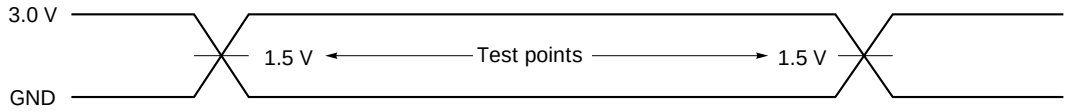
Remark 1. V_{IN}: Input voltage

2. These parameters are periodically sampled and not 100 % tested.

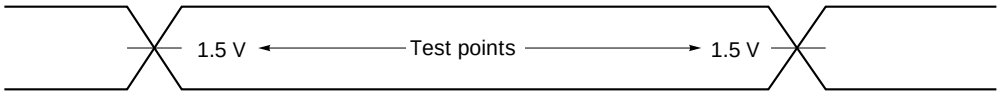
AC Characteristics (Recommended operating conditions unless otherwise noted)

AC Test Conditions

Input waveform (Rise/fall time ≦ 3 ns)



Output waveform



Output load

AC Characteristics directed with the note should be measured with the output load shown in **Fig. 1** or **Fig. 2.**

Fig. 1

(For t_{AA}, t_{ACS}, t_{OE}, t_{OH})

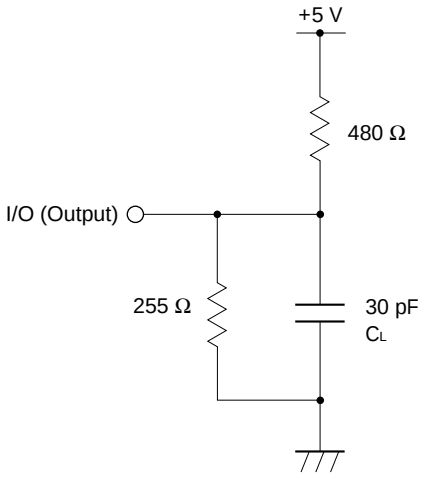
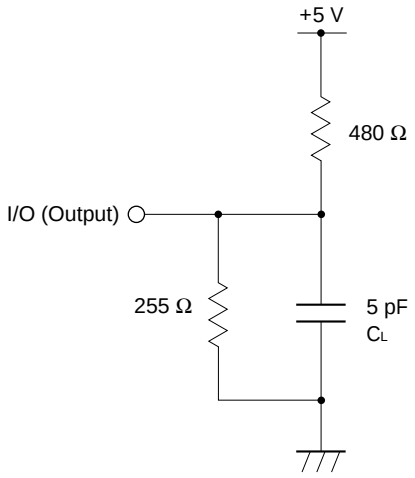


Fig. 2

(For t_{CHZ}, t_{CLZ}, t_{OHZ}, t_{OLZ}, t_{WHZ}, t_{OW})



Remark C_L includes capacitances of the probe and jig, and stray capacitances.

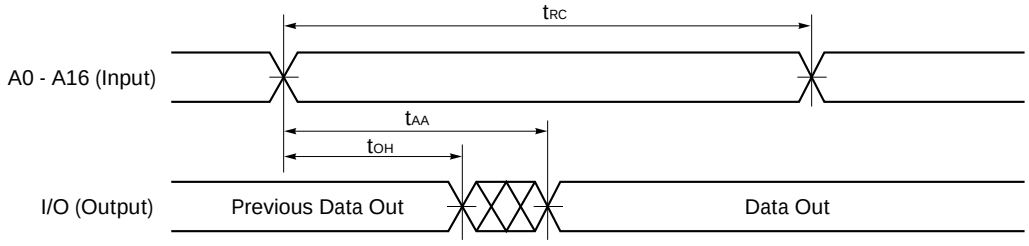
Read Cycle

Parameter	Symbol	μPD431008LE-15		μPD431008LE-17		μPD431008LE-20		Unit	Condition
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t_{RC}	15		17		20		ns	
Address access time	t_{AA}		15		17		20	ns	**Note 1.**
$\overline{CS}$ access time	t_{ACS}		15		17		20	ns	
$\overline{OE}$ access time	t_{OE}		8		9		10	ns	
Output hold from address change	t_{OH}	5		5		5		ns	
$\overline{CS}$ to output in low-Z	t_{CLZ}	5		5		5		ns	**Note 2.**
$\overline{OE}$ to output in low-Z	t_{OLZ}	1		1		1		ns	
$\overline{CS}$ to output in high-Z	t_{CHZ}		7		7		7	ns	
$\overline{OE}$ to output in high-Z	t_{OHZ}		7		7		7	ns	

Note 1. See the output load shown in **Fig. 1**.

2. See the output load shown in **Fig. 2**.

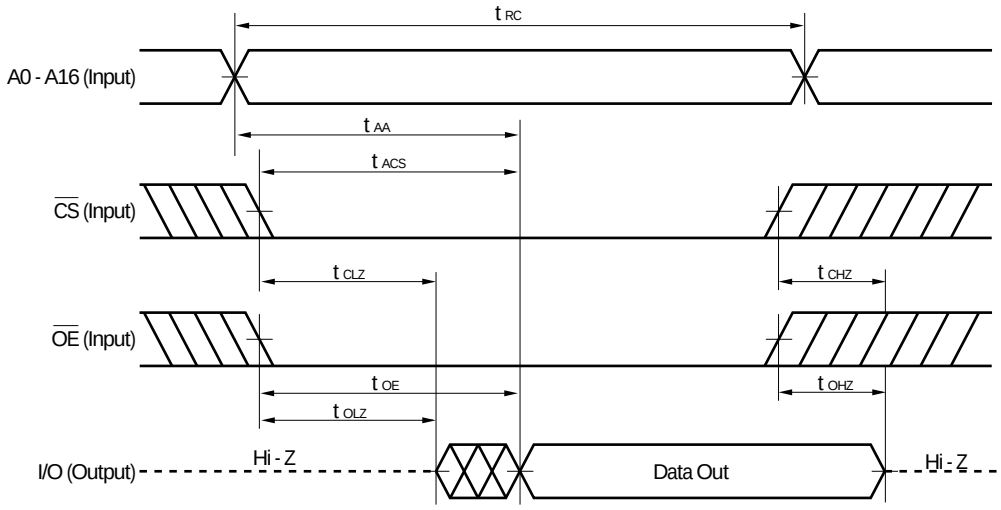
Read Cycle Timing Chart 1 (Address Access)



Remark 1. In read cycle, $\overline{WE}$ should be fixed to high level.

2. $\overline{CS}$ = $\overline{OE}$ = V_{IL}

Read Cycle Timing Chart 2 ($\overline{CS}$ Access)



Caution Address valid prior to or coincident with $\overline{CS}$ low level input.

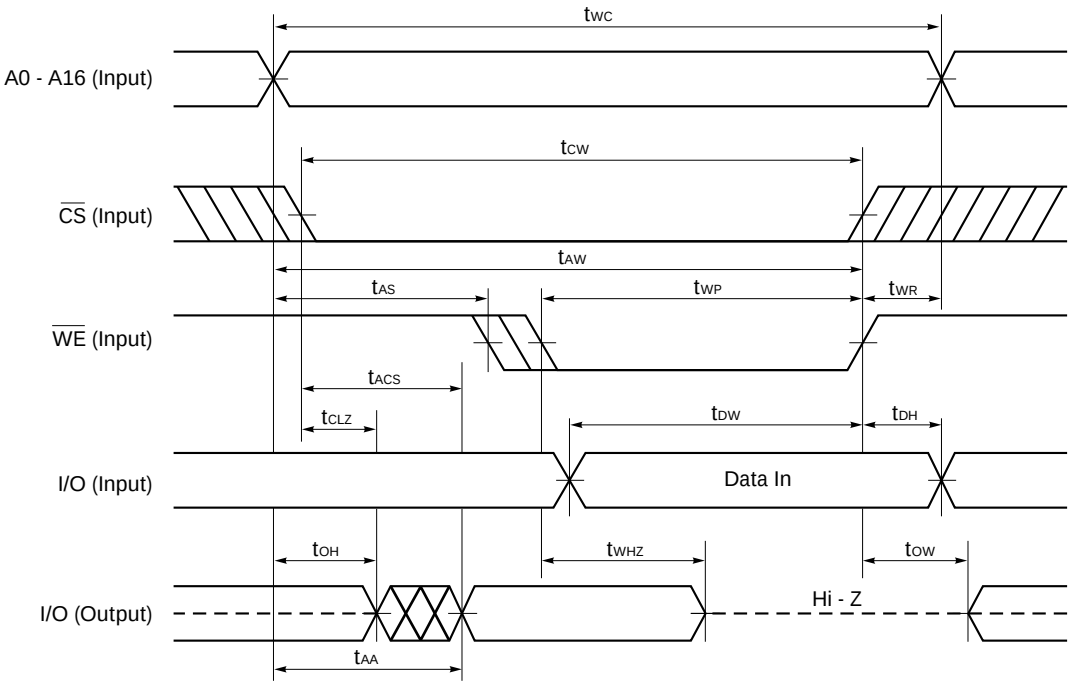
Remark In read cycle, $\overline{WE}$ should be fixed to high level.

Write Cycle

Parameter	Symbol	μPD431008LE-15		μPD431008LE-17		μPD431008LE-20		Unit	Condition
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	t_{WC}	15		17		20		ns	
$\overline{CS}$ to end of write	t_{CW}	10		11		12		ns	
Address valid to end of write	t_{AW}	9		11		12		ns	
Write pulse width	t_{WP}	9		10		10		ns	
Data valid to end of write	t_{DW}	8		9		10		ns	
Data hold time	t_{DH}	0		0		0		ns	
Address setup time	t_{AS}	0		0		0		ns	
Write recovery time	t_{WR}	0		0		0		ns	
$\overline{WE}$ to output in high-Z	t_{WHZ}		7		7		7	ns	Note
Output active from end of write	t_{OW}	3		3		3		ns	

Note See the output load shown in **Fig. 2**.

Write Cycle Timing Chart 1 ($\overline{WE}$ Controlled)



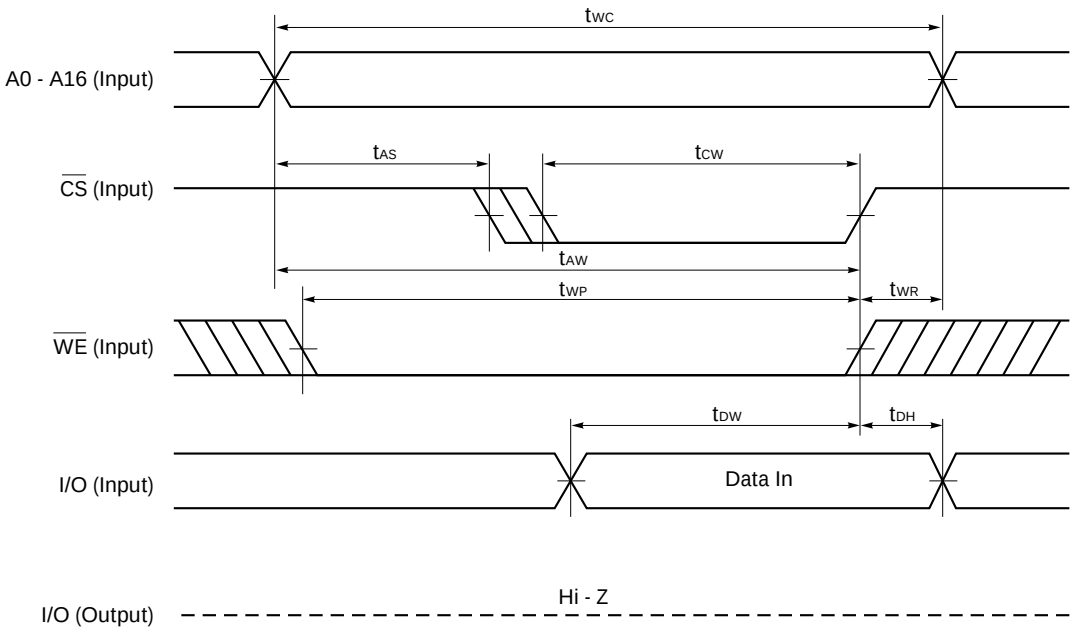
Caution $\overline{CS}$ or $\overline{WE}$ should be fixed to high level during address transition.

Remark 1. Write operation is done during the overlap time of a low level $\overline{CS}$ and a low level $\overline{WE}$.

2. During t_{WHZ}, I/O pins are in the output state, therefore the input signals of opposite phase to the output must not be applied.

3. When $\overline{WE}$ is at low level, the I/O pins are always Hi-Z. When $\overline{WE}$ is at high level, read operation is executed. Therefore $\overline{OE}$ should be at high level to make the I/O pins Hi-Z.

Write Cycle Timing Chart 2 ($\overline{CS}$ Controlled)

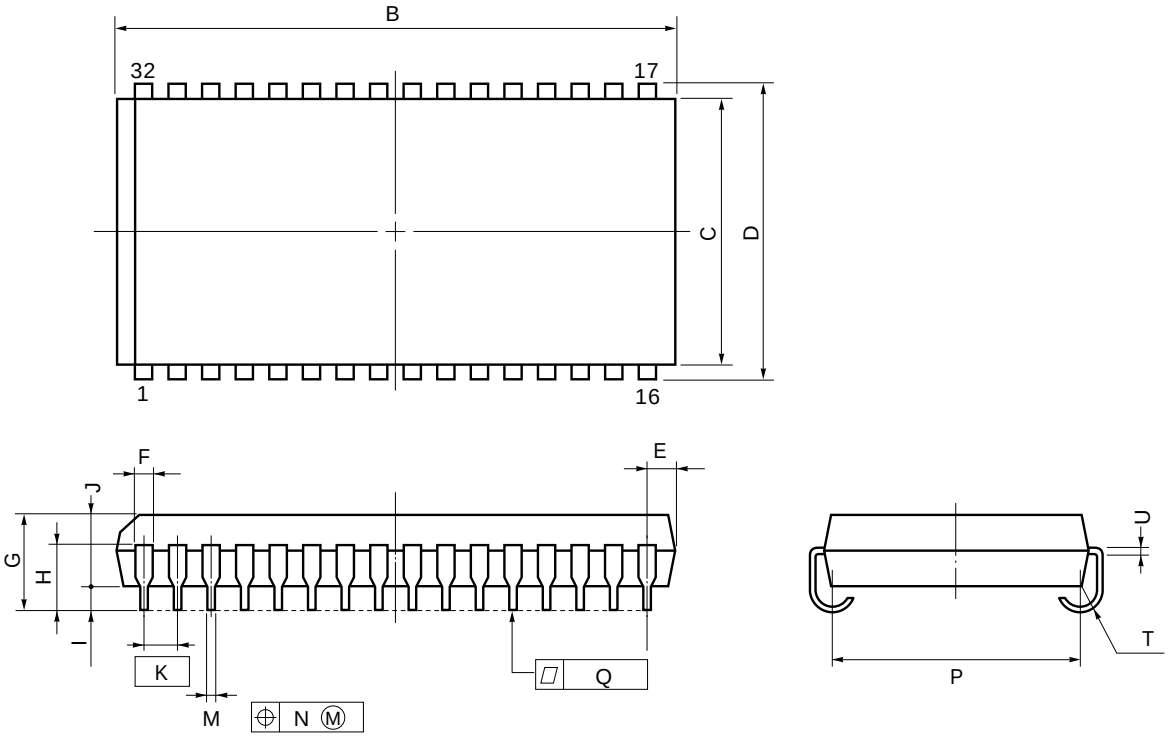


Caution $\overline{CS}$ or $\overline{WE}$ should be fixed to high level during address transition.

Remark Write operation is done during the overlap time of a low level $\overline{CS}$ and a low level $\overline{WE}$.

Package Drawing

32 PIN PLASTIC SOJ (400 mil)



P32LE-400A

NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
B	21.06±0.2	0.829±0.008
C	10.16	0.400
D	11.18±0.2	0.440±0.008
E	1.005±0.1	$0.040^{+0.004}_{-0.005}$
F	0.74	0.029
G	3.5±0.2	0.138±0.008
H	2.545±0.2	0.100±0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	9.4±0.20	0.370±0.008
Q	0.1	0.004
T	R 0.85	R 0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

RECOMMENDED SOLDERING CONDITIONS

Please consult with our sales offices for soldering conditions of the μPD431008.

TYPE OF SURFACE MOUNT DEVICE

μPD431008LE: 32-pin plastic SOJ (400 mil)

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

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